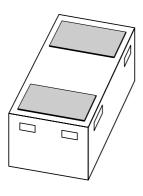
DISCRETE SEMICONDUCTORS

DATA SHEET



1PS10SB82Schottky barrier diode

Product data sheet 2003 Aug 20



NXP Semiconductors Product data sheet

Schottky barrier diode

1PS10SB82

FEATURES

- · Low forward voltage
- · Low diode capacitance
- Leadless ultra small plastic package (1.0 mm × 0.6 mm × 0.5 mm)
- Boardspace 1.17 mm² (approx. 10% of SOT23)
- Power dissipation comparable to SOT23.

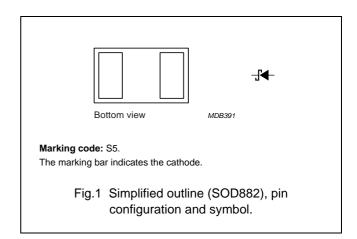
APPLICATIONS

- UHF mixers
- · Sampling circuits
- Modulators
- · Phase detectors
- Mobile communication, digital (still) cameras, PDA's and PCMCIA cards.

DESCRIPTION

An epitaxial Schottky barrier diode encapsulated in a SOD882 leadless ultra small plastic package.

ESD sensitive device, observe handling precautions.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER		MAX.	UNIT
V_R	continuous reverse voltage	-	15	٧
I _F	continuous forward current		30	mA
T _{stg}	storage temperature		+150	°C
Tj	junction temperature		150	°C

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	forward voltage	see Fig.2			
		I _F = 1 mA	_	340	mV
		I _F = 30 mA	_	700	mV
r _D	differential diode forward resistance	$f = 1 \text{ MHz}$; $I_F = 5 \text{ mA}$; see Fig.5	12	_	Ω
I _R	continuous reverse current	V _R = 1 V; see Fig.3; note 1	_	0.2	μΑ
C _d	diode capacitance	$V_R = 0 \text{ V}$; f = 1 MHz; see Fig.4	1	_	pF

Note

1. Pulse test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Refer to SOD882 standard mounting conditions (footprint), FR4 with 60 μm copper strip line.

Soldering

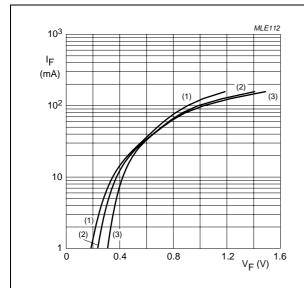
Reflow soldering is the only recommended soldering method.

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Schottky barrier diode

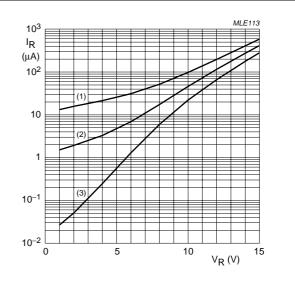
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GRAPHICAL DATA



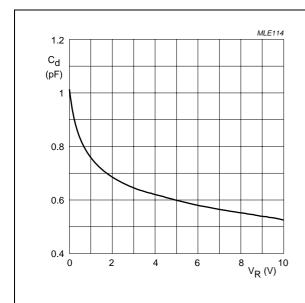
- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



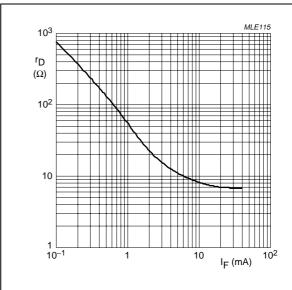
- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; T_{amb} = 25 °C.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.



f = 1 MHz; T_{amb} = 25 °C.

Fig.5 Differential diode forward resistance as a function of forward current; typical values.

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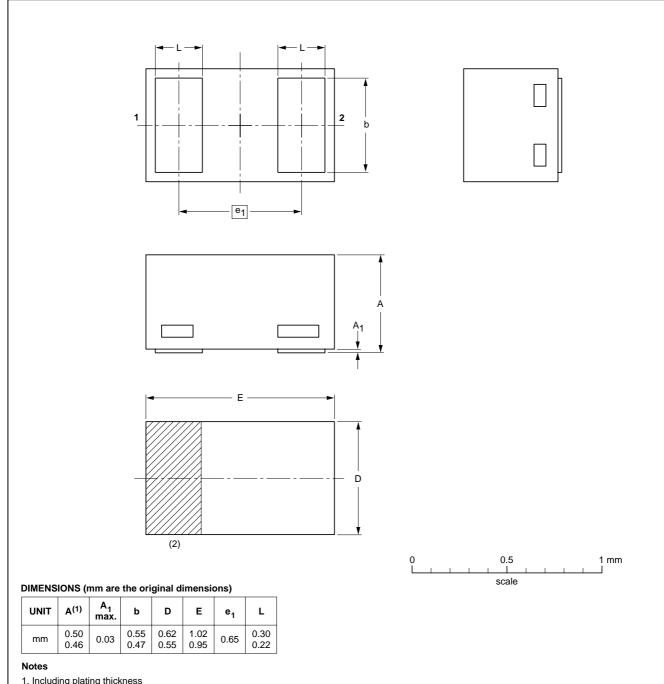
Schottky barrier diode

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PACKAGE OUTLINE

Leadless ultra small plastic package; 2 terminals; body 1.0 x 0.6 x 0.5 mm

SOD882



- 1. Including plating thickness
- 2. The marking bar indicates the cathode

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOD882						03-04-16 03-04-17	

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

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